BT136-600E



4Q Triac

Rev. 04 — 1 April 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated sensitive gate four quadrant triac in a SOT78 plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

1.2 Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

1.3 Applications

General purpose motor control

General purpose switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; see Figure 4; see Figure 5	-	-	25	Α
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	4	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I _{GT} gate trigger current	0 00	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$	-	2.5	10	mA
	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 7}}{\text{Figure 7}}$	-	4	10	mA	
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$	-	5	10	mA
	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+; $ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 7}}{}$	-	11	25	mA	
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 9</u>	-	2.2	15	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		. .
2	T2	main terminal 2	mb	T2—T1
3	G	gate		`G sym051
mb	T2	mounting base; main terminal 2		
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT136-600E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78
BT136-600E/L01	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 107 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	4	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	25	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$; see Figure 5; see Figure 4	-	27	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	3.1	A ² s
dl _T /dt	rate of rise of on-state current	$I_T = 6 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; $T2+G+$	-	50	A/µs
		$I_T = 6 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; $T2+G$ -	-	50	A/µs
		$I_T = 6 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; T2- G-	-	50	A/µs
		$I_T = 6 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	Α
V_{GM}	peak gate voltage		-	5	V
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

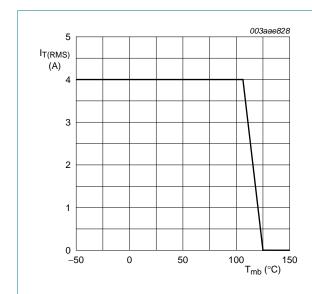
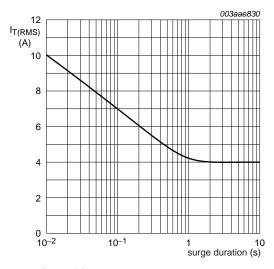


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz $T_{mb} \le 107 \text{ }^{\circ}\text{C}$

Fig 2. RMS on-state current as a function of surge duration; maximum values

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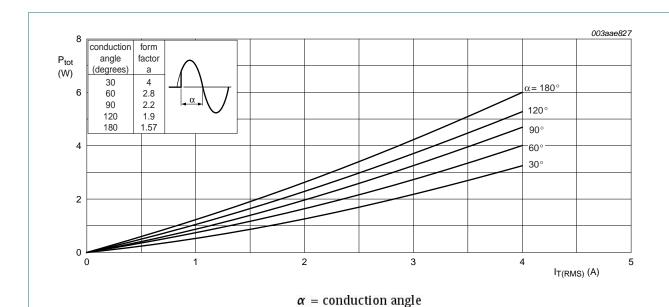


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

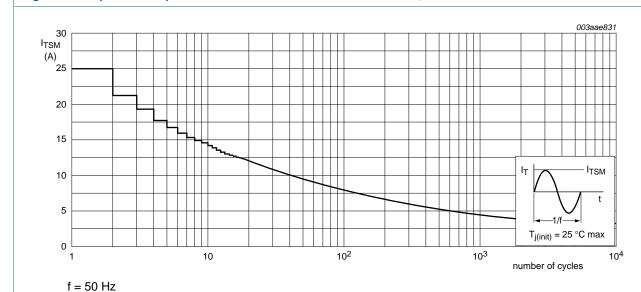
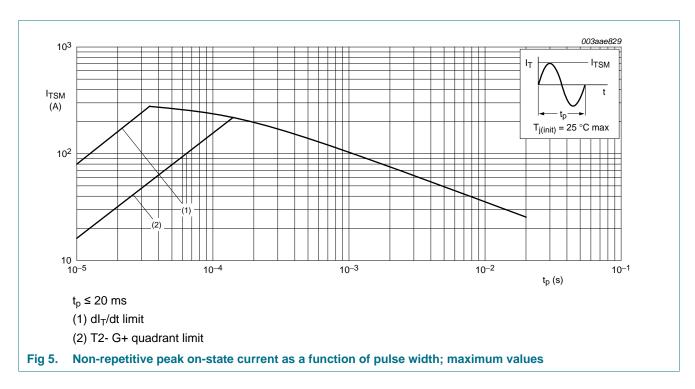


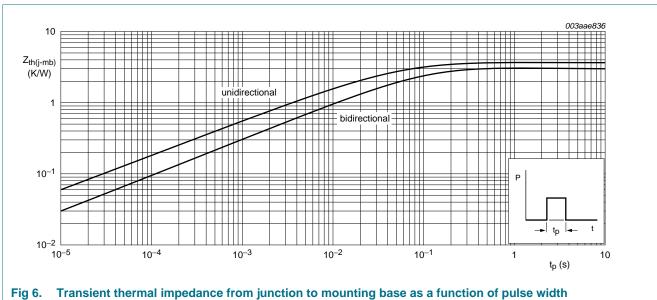
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



Thermal characteristics 5.

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ui(j iiib)	thermal resistance from	half cycle; see Figure 6	-	-	3.7	K/W
	junction to mounting base	full cycle; see Figure 6	-	-	3	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

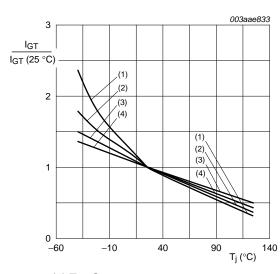


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6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	4	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	11	25	mA
I _L latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	3	15	mA	
	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	10	20	mA	
	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	2.5	15	mA	
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	4	20	mA
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$	-	2.2	15	mΑ
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; see <u>Figure 10</u>	-	1.4	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mΑ
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; exponential waveform; gate open circuit	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 6 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig 7. Normalized gate trigger current as a function of junction temperature

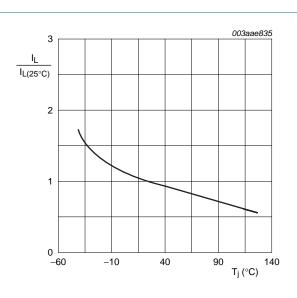


Fig 8. Normalized latching current as a function of junction temperature

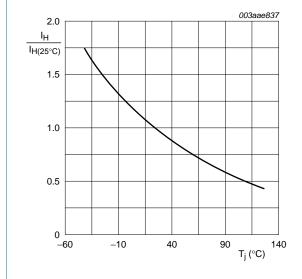
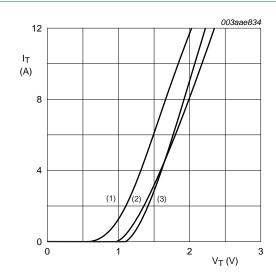


Fig 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.27 \text{ V}$

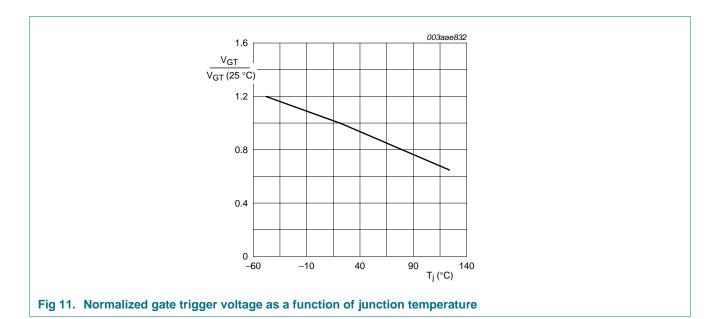
 $R_s = 0.091 \Omega$

(1) T_i = 125 °C; typical values

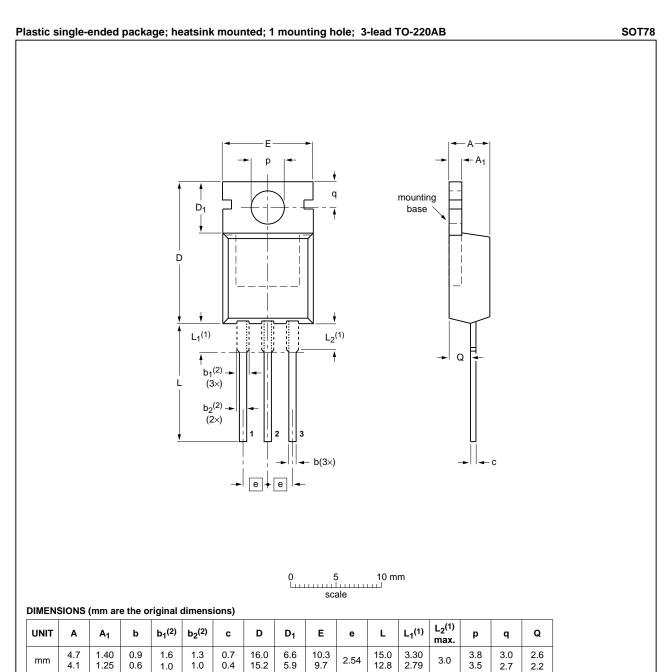
(2) T_j = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage



7. Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFERENCES			EUROPEAN ISSUE DA	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig 12. Package outline SOT78 (TO-220AB)

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Product data sheet

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BT136-600E v.4	20110401	Product data sheet	-	BT136-600E v.3
Modifications:	 Various chang 	es to content.		
BT136-600E v.3	20100831	Product data sheet	-	BT136_SERIES_E v.2

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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